



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Tomoyoshi KUSHIDA

U.S. Application No. 09/435,766

Filed: November 8, 1999

Group Art Unit: 2811

Examiner: S. Loke

Docket No.: 104361

For: SEMICONDUCTOR DEVICE HAVING REDUCED ON RESISTANCE (As Amended)

AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

In reply to the Office Action mailed March 2, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 5-10 and 14-19 without prejudice or disclaimer.

Please amend claim 12 as follows:

12. (Twice Amended) A semiconductor device comprising:
- a substrate having a first conductive type;
 - a drift region having the first conductive type and disposed on the substrate;
 - a channel region having a second conductive type different from the first
- conductive type and provided on the drift region;
- a gate region provided so as to surround at least the channel region via an insulation film; and

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Sub
original
claims 12, 13
B1
figs. 9B, 10B